

Amendments to the Specification:

Please replace paragraph [0008] with the following rewritten paragraph:

[0008] Wafer induced shift (i.e., errors in the measurement results due to wafer induced shift) occurs due to characteristics of the patterned layers formed on the substrate. One cause of WIS is an asymmetric (non-uniform) processing that is performed on the film layers formed on the substrate. For example, if a step that removes or polishes part of a layer from the substrate, or if a step that deposits a layer onto the substrate, is not performed uniformly over the entire substrate, it may cause WIS. For example, certain layers are made very thin by performing a chemical mechanical planarization (CMP) process on that layer in order to remove a part of the thickness of the layer. This CMP process typically is performed using a rotating disk that is contacted with the uppermost layer on the substrate in order to remove part of that layer. Since the speed of the disk at its outer perimeter is higher than the speed of the disk near its center, different effects can be caused on the substrate layer near the outer perimeter of the disk compared to the inner (center) portion of the disk. For example, the directions of throughholes can become tilted (in the direction in which the disk rotates) as one progresses from the center of the substrate toward the outer perimeter thereof. In addition, during deposition, typically a source of the deposited material is located above the substrate at the location of the central axis of the substrate. The vaporized particles to be deposited on the substrate are emitted from this point source, and can become deposited unequally between the center and outer perimeter of the substrate. These asymmetric processing steps can cause WIS errors in the measurements made during the overlay measurement process. WIS should be compensated for as well as TIS. However, WIS compensation is very difficult and therefore is not done very frequently, as described below.